L Number	Hits	Search Text	DB	Time stamp
1	6	"6180995"	USPAT; US-PGPUB; EPO; JPO	2004/09/07 07:02
2	9	"6307247"	USPAT; US-PGPUB; EPO; JPO	2004/09/07 07:03
3	13	"6287979"	USPAT; US-PGPUB; EPO; JPO	2004/09/07 07:03
4	16	"4634494"	USPAT; US-PGPUB; EPO; JPO	2004/09/07 07:03
5	19	"5742091"	USPAT; US-PGPUB; EPO; JPO	2004/09/07 07:03
6	16	"6303423"	USPAT; US-PGPUB; EPO; JPO	2004/09/07 07:03
7	72	"6180995" "6307247" "6287979" "4634494" "5742091" "6303423"	USPAT; US-PGPUB; EPO; JPO	2004/09/07 07:04
8	39	inductor and (oxide adj layer) and ("low-k" adj dielectric)	USPAT; US-PGPUB; EPO; JPO	2004/09/07 07:15
10	3	(inductor and (oxide adj layer) and ("low-k" adj dielectric)) and (air adj gap)	USPAT; US-PGPUB; EPO; JPO	2004/09/07 07:15
9	39	(inductor and (oxide adj layer) and ("low-k" adj dielectric)) and (method process)	USPAT; US-PGPUB; EPO; JPO	2004/09/07 07:06
11	120	inductor and oxide and ("low-k" near1 (insulation dielectric))	USPAT; US-PGPUB; EPO; JPO	2004/09/07 07:15
12	17	(inductor and oxide and ("low-k" near1 (insulation dielectric))) and (air adj gap)	USPAT; US-PGPUB; EPO; JPO	2004/09/07 07:15
13	0	inductor and (oxide with ("low-k" near1 (insulation dielectric)) with (air adj gap))	USPAT; US-PGPUB; EPO; JPO	2004/09/07 07:17
14	0	inductor and (oxide with "low-k" with (air adj gap))	USPAT; US-PGPUB; EPO; JPO	2004/09/07 07:18
15	0	inductor and (oxide near1 layer) and ("low-k" with (air adj gap))	USPAT; US-PGPUB; EPO; JPO	2004/09/07 07:19
16	31	inductor and (oxide near1 layer) and (("low-k" dielectric) with (air adj gap))	USPAT; US-PGPUB; EPO; JPO	2004/09/07 07:19
17	0	6495903.URPN.	USPAT	2004/09/07 07:23
18	8	("5539241" | "5831331" | "6153489" | "6180433" | "6221727" | "6242791" | "6274920" | "6287931").PN.	USPAT	2004/09/07 07:23
19	67	("6180995" "6307247" "6287979" "4634494" "5742091" "6303423") not ((inductor and (oxide adj layer) and ("low-k" adj dielectric)) and (method process)) not ((inductor and oxide and ("low-k" near1 (insulation dielectric))) and (air adj gap)) not (inductor and (oxide near1 layer) and (("low-k" dielectric) with (air adj gap)))	USPAT; US-PGPUB; EPO; JPO	2004/09/07 08:19
20	17	"6413827"	USPAT; US-PGPUB; EPO; JPO	2004/09/07 08:19
21	0	6413827.pn. and inductor	USPAT; US-PGPUB; EPO; JPO	2004/09/07 08:20
22	0	"sc12765tp"	USPAT; US-PGPUB; EPO; JPO	2004/09/07 09:30

23	14	(low adj k adj dielectric) with (semiconductor adj fabrication adj process)	USPAT; US-PGPUB; EPO; JPO	2004/09/07 09:37
24	8564763	US -6,486,061 B1 US -6,472,325 B1 US -6,465,372 B1 US -6,455,443 B1 US -6,440,878 B1 US -6,383,913 B1 US -6,348,407 B1 US -6,331,420 B1 US -6,303,525 B1 US -6,197,704 B1 US -6,153,512	USPAT; US-PGPUB; EPO; JPO	2004/09/07 09:38
25	11	6486061.pn. 6472325.pn. 6465372.pn. 6455443.pn. 6440878.pn. 6383913.pn. 6348407.pn. 6331420.pn. 6303525.pn. 6197704.pn. 6153512.pn.	USPAT; US-PGPUB; EPO; JPO	2004/09/07 09:47
26	0	(substrate wafer) with (second near2 (low adj k)) with void with polish$3	USPAT; US-PGPUB; EPO; JPO	2004/09/07 09:50
27	1	(substrate wafer) with (low adj "k") with void with polish$3	USPAT; US-PGPUB; EPO; JPO	2004/09/07 09:52
28	1	(substrate wafer) with (low adj "k") with (void (via adj hole)) with polish$3	USPAT; US-PGPUB; EPO; JPO	2004/09/07 09:52
29	11	(substrate wafer) with (low adj "k") with (void via hole) with polish$3	USPAT; US-PGPUB; EPO; JPO	2004/09/07 10:10
30	8	((substrate wafer) with (low adj "k") with (void via hole) with polish$3) and cvd	USPAT; US-PGPUB; EPO; JPO	2004/09/07 10:11
31	8	(((substrate wafer) with (low adj "k") with (void via hole) with polish$3) and cvd) and cmp	USPAT; US-PGPUB; EPO; JPO	2004/09/07 10:11